

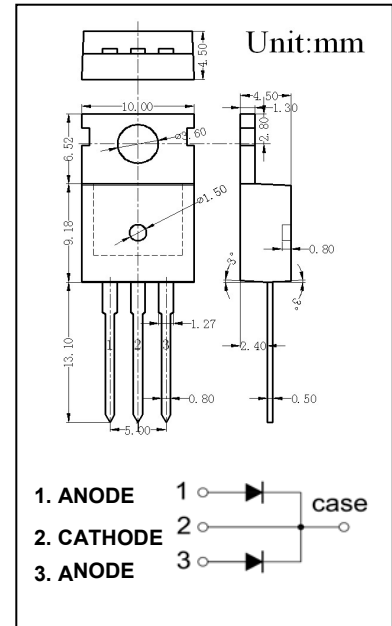


TO-220 Plastic-Encapsulate Diodes

201 00 SCHOTTKY BARRIER RECTIFIER

FEATURES

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss,High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters,Free Wheeling, and Polarity Protection Applications



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{RRM}	Peak repetitive reverse voltage	100	V
V_{RWM}	Working peak reverse voltage		
V_R	DC blocking voltage		
$V_{R(RMS)}$	RMS reverse voltage	70	V
I_o	Average rectified output current@ $T_c=125^\circ\text{C}$	20	A
I_{FSM}	Non-Repetitive peak forward surge current 8.3ms half sine wave	120	A
P_D	Power dissipation	2	W
$R_{\theta JA}$	Thermal resistance from junction to ambient	50	$^\circ\text{C}/\text{W}$
T_j	Junction temperature	125	$^\circ\text{C}$
T_{stg}	Storage temperature	-55~+150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=1\text{mA}$	100			V
Reverse current	I_R	$V_R=100\text{V}$			0.1	mA
Forward voltage	V_{F1}	$I_{F1}=10\text{A}$			1	V
Forward voltage	V_{F2^*}	$I_{F2}=20\text{A}$			1.2	V

Typical Characteristics

